

Digital transistors (built in resistor)

DTB143TK / DTB143TS

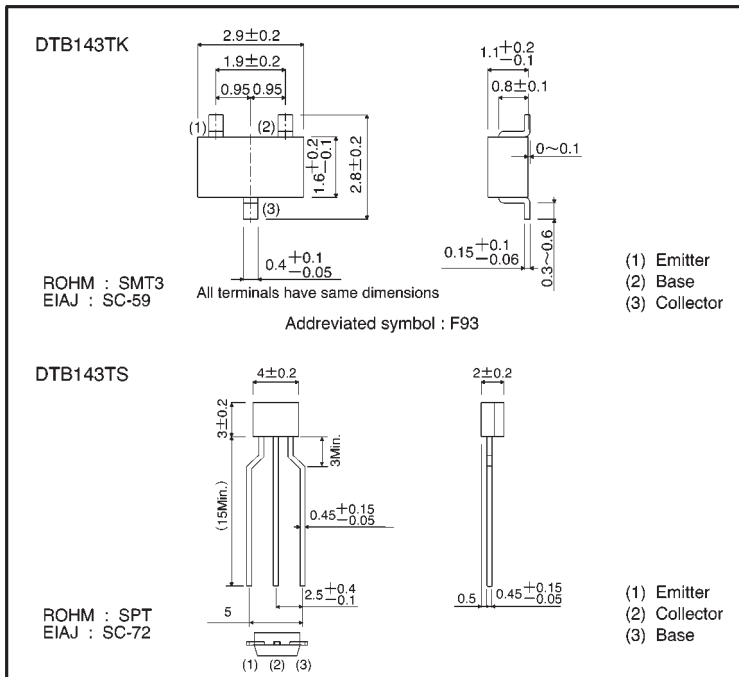
●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making device design easy.

●Structure

PNP digital transistor
(Built-in resistor type)

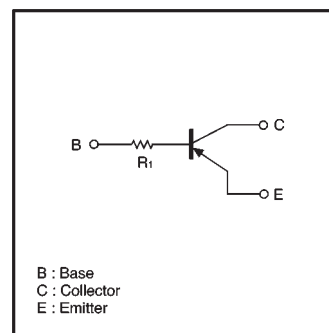
●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits(DTB143T□)		Unit
		K	S	
Collector-base voltage	V _{CB0}	-50		V
Collector-emitter voltage	V _{CE0}	-40		V
Emitter-base voltage	V _{EB0}	-5		V
Collector current	I _c	-500		mA
Collector power dissipation	P _c	200	300	mW
Junction temperature	T _j	150		°C
Storage temperature	T _{stg}	-55~+150		°C

●Equivalent circuit



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-50	—	—	V	I _C = -50 μA
Collector-emitter breakdown voltage	BV _{CEO}	-40	—	—	V	I _C = -1mA
Emitter-base breakdown voltage	BV _{EBO}	-5	—	—	V	I _E = -50 μA
Collector cutoff current	I _{CBO}	—	—	-0.5	μA	V _{CB} = -50V
Emitter cutoff current	I _{EBO}	—	—	-0.5	μA	V _{EB} = -4V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	-0.3	V	I _C /I _B = -50mA/-2.5mA
DC current transfer ratio	h _{FE}	100	250	600	—	V _{CE} = -5V, I _C = -50mA
Input resistance	R _i	3.29	4.7	6.11	kΩ	—
Transition frequency	f _t	—	200	—	MHz	V _{CE} = -10V, I _E = 50mA, f = 100MHz *

* Transition frequency of the device

●Packaging specifications

Part No.	Package	SMT3	SPT
	Packaging type	Taping	Taping
	Code	T146	TP
	Basic ordering unit (pieces)	3000	5000
DTB143TK		○	—
DTB143TS		—	○

●Electrical characteristic curves

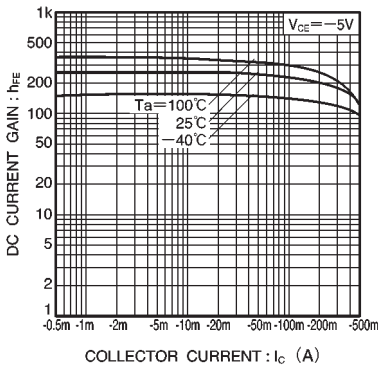


Fig.1 DC current gain vs. collector current

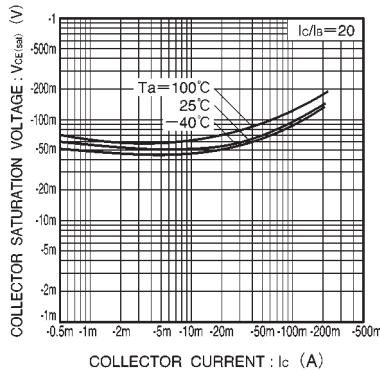


Fig.2 Collector-emitter saturation voltage vs. collector current